

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,734,480 B2
DATED : May 11, 2004
INVENTOR(S) : Chung et al.

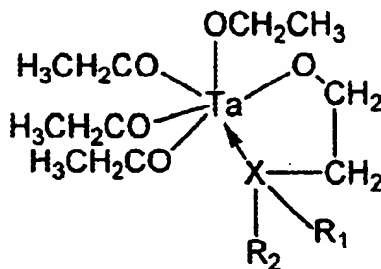
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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [57], **ABSTRACT**, should read as follows:

-- Semiconductor capacitors comprise first electrodes, second electrodes, and tantalum oxide layers positioned between the first electrodes and the second electrodes. The tantalum oxide layers are formed by depositing at least one precursor and ozone gas, the at least one precursor represented by the formula:



wherein X is selected from the group consisting of nitrogen, sulfur, oxygen, and a carbonyl group; and
wherein R₁ and R₂ are independently alkyl. --.

Signed and Sealed this

Eighteenth Day of October, 2005

JON W. DUDAS
Director of the United States Patent and Trademark Office